



Cite this: *RSC Adv.*, 2017, 7, 9772

Correction: A non-volatile resistive memory effect in 2,2',6,6'-tetraphenyl-dipyranylidene thin films as observed in field-effect transistors and by conductive atomic force microscopy

Marc Courté,^a Sandeep G. Surya,^b Ramesh Thamankar,^c Chao Shen,^a
V. Ramgopal Rao,^b Subodh G. Mhaisalkar^{de} and Denis Fichou^{*afg}

DOI: 10.1039/c7ra90012k

www.rsc.org/advances

Correction for 'A non-volatile resistive memory effect in 2,2',6,6'-tetraphenyl-dipyranylidene thin films as observed in field-effect transistors and by conductive atomic force microscopy' by Marc Courté *et al.*, *RSC Adv.*, 2017, 7, 3336–3342.

The authors regret that the name of the sixth author was presented incorrectly in the original article. Subodh G. Mhaisalkar's name has been corrected herein.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^aSchool of Physical and Mathematical Sciences, Nanyang Technological University, 637371, Singapore. E-mail: denisfichou@ntu.edu.sg

^bDepartment of Electrical Engineering, Indian Institute of Technology Bombay, Mumbai 400 076, India

^cSchool of Engineering and Technology, CMR University, Bangalore 560043, India

^dSchool of Material Science and Engineering, Nanyang Technological University, 639798, Singapore

^eEnergy Research Institute@NTU (ERI@N), Nanyang Technological University, 637141, Singapore

^fCNRS, UMR 8232, Institut Parisien de Chimie Moléculaire, F-75005, Paris, France

^gSorbonne Universités, UPMC Univ Paris 06, UMR 8232, Institut Parisien de Chimie Moléculaire, F-75005, Paris, France

